

Micromachined Coplanar Waveguides in CMOS Technology

V. Milanovic, M. Gaitan, E.D. Bowen and M.E. Zaghloul. "Micromachined Coplanar Waveguides in CMOS Technology." 1996 Microwave and Guided Wave Letters 6.10 (Oct. 1996 [MGWL]): 380-382.

Coplanar waveguides were fabricated in standard complimentary metal-oxide semiconductor (CMOS) with post-processing micromachining. IC'S were designed with commercial CAD tools, fabricated through the MOSIS/sup 1/ service, and subsequently suspended by maskless top-side etching. Absence of the lossy silicon substrate after etching results in significantly improved insertion loss characteristics, dispersion characteristics, and phase velocity. Measurements were performed at frequencies from 1 to 40 GHz, before and after micromachining. These show improvement in loss characteristics of orders of magnitude. For the micromachined line, loss does not exceed 4 dB/cm. Before etching, loss as high as 38 dB/cm is measured. Phase velocity $V_{\text{sub P}}/0.8 - c$ is achieved for the micromachined line,

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